

HAT1038R, HAT1038RJ

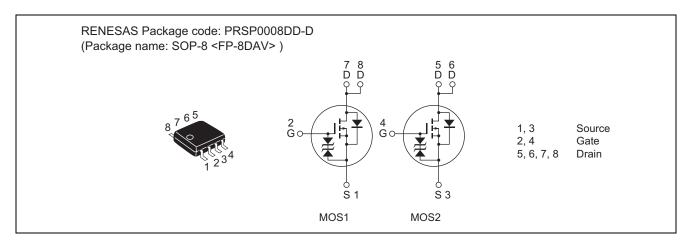
Silicon P Channel Power MOS FET High Speed Power Switching

REJ03G1150-0600 Rev.6.00 Aug 25, 2009

Features

- For Automotive Application (at Type Code "J")
- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item		Symbol	Value	Unit
Drain to source voltage		$V_{\rm DSS}$	-60	V
Gate to source voltage		V _{GSS}	±20	V
Drain current		I _D	-3.5	Α
Drain peak current		I _{D (pulse)} Note 1	-28	Α
Body-drain diode reverse drain current		I _{DR}	-3.5	Α
Avalanche current	HAT1038R	I _{AP} Note 4	_	_
	HAT1038RJ		-3.5	Α
Avalanche energy	HAT1038R	E _{AR} Note 4	_	_
	HAT1038RJ		1.05	mJ
Channel dissipation		Pch Note 2	2	W
Channel dissipation		Pch Note 3	3	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. 1 Drive operation: When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW ≤ 10 s
- 3. 2 Drive operation: When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW ≤ 10 s
- 4. Value at Tch = 25°C, Rg \geq 50 Ω

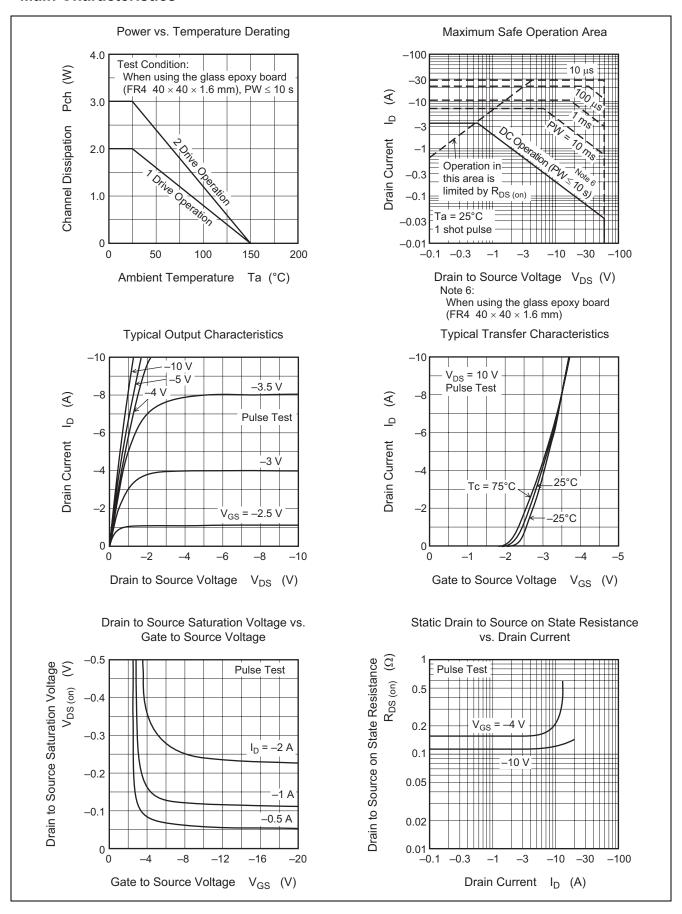
Electrical Characteristics

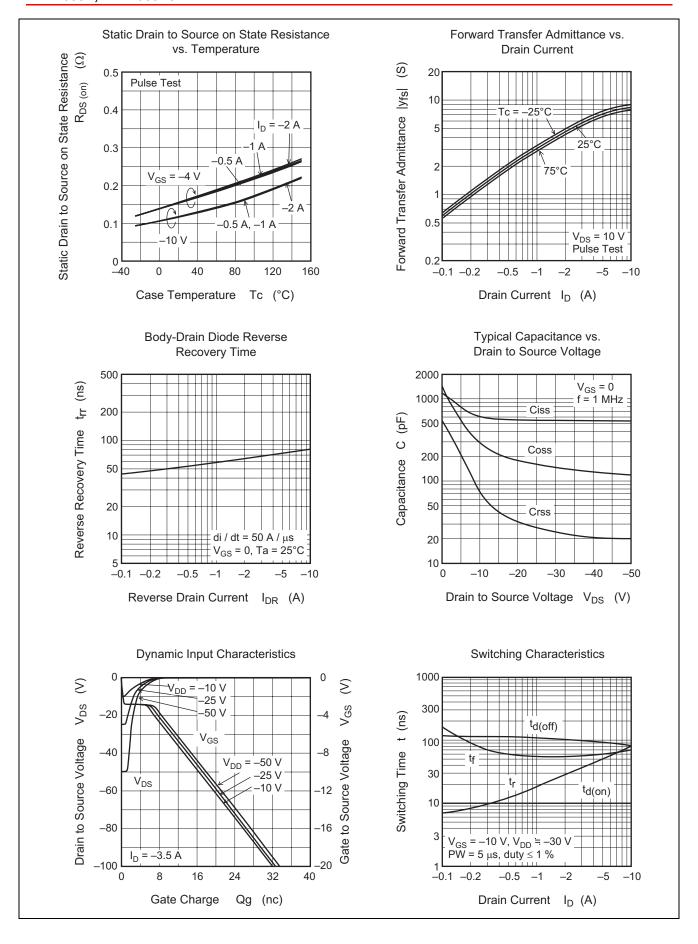
 $(Ta = 25^{\circ}C)$

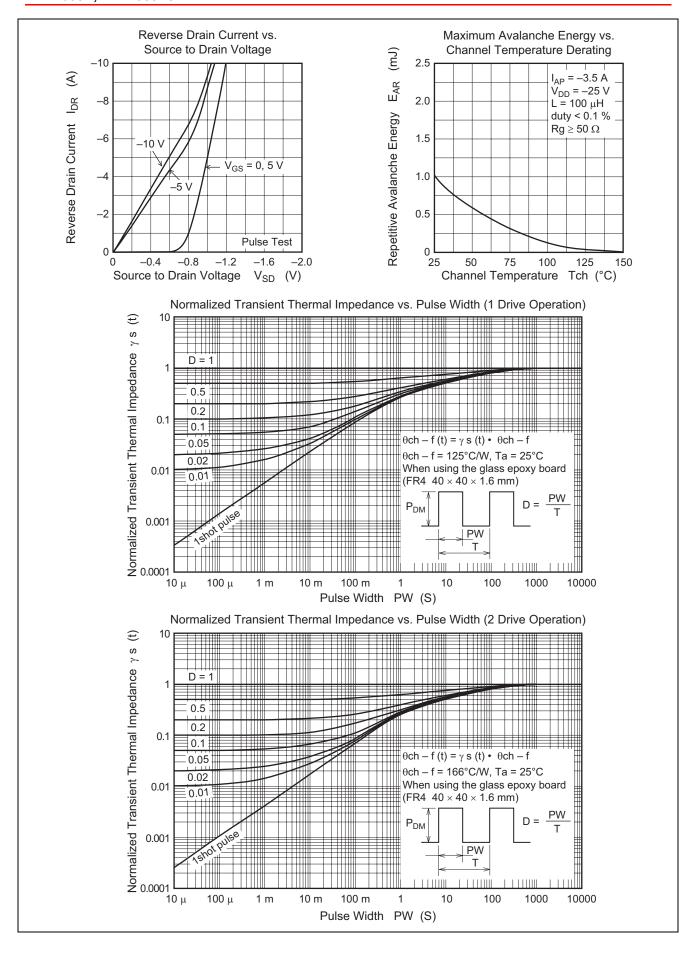
Item		Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage		V _{(BR) DSS}	-60	_	_	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source leak voltage		V _{(BR) GSS}	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I _{GSS}	_	_	±10	μА	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain	HAT1038R	I _{DSS}			-1	μΑ	$V_{DS} = -60 \text{ V}, V_{GS} = 0$
current	HAT1038RJ	I _{DSS}	_	_	-0.1	μА	
Zero gate voltage drain	HAT1038R	I _{DSS}	_	_	_	μА	$V_{DS} = -48 \text{ V}, V_{GS} = 0$
current	HAT1038RJ	I _{DSS}	_	_	-10	μА	Ta = 125°C
Gate to source cutoff voltage		V _{GS (off)}	-1.2	_	-2.2	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Static drain to source on state resistance		R _{DS (on)}	_	0.12	0.15	Ω	$I_D = -2 \text{ A}, V_{GS} = -10 \text{ V}^{\text{Note 5}}$
		R _{DS (on)}	_	0.16	0.23	Ω	$I_D = -2 \text{ A}, V_{GS} = -4 \text{ V}^{\text{Note 5}}$
Forward transfer admittance		y _{fs}	3	4.5	_	S	$I_D = -2 \text{ A}, V_{DS} = -10 \text{ V}^{\text{Note 5}}$
Input capacitance		Ciss	_	600	_	pF	V _{DS} = -10 V
Output capacitance		Coss	_	290	_	pF	$V_{GS} = 0$
Reverse transfer capacitance		Crss	_	75	_	pF	f = 1 MHz
Turn-on delay time		t _{d (on)}	_	11	_	ns	$V_{GS} = -10 \text{ V}, I_D = -2 \text{ A},$
Rise time		t _r	_	30	_	ns	V _{DD} ≅ -30 V
Turn-off delay time		t _{d (off)}	_	100	_	ns	
Fall time		t _f	_	55	_	ns	
Body-drain diode forward voltage		V_{DF}	_	-0.98	-1.28	V	$I_F = -3.5 \text{ A}, V_{GS} = 0^{\text{Note 5}}$
Body-drain diode reverse recovery time		t _{rr}	_	70	_	ns	$I_F = -3.5 \text{ A}, V_{GS} = 0$
							di _F /dt = 50 A/μs

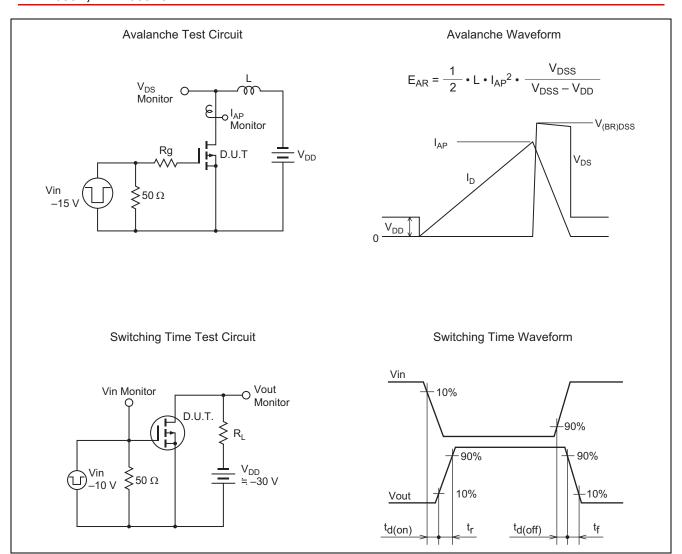
Note: 5. Pulse test

Main Characteristics

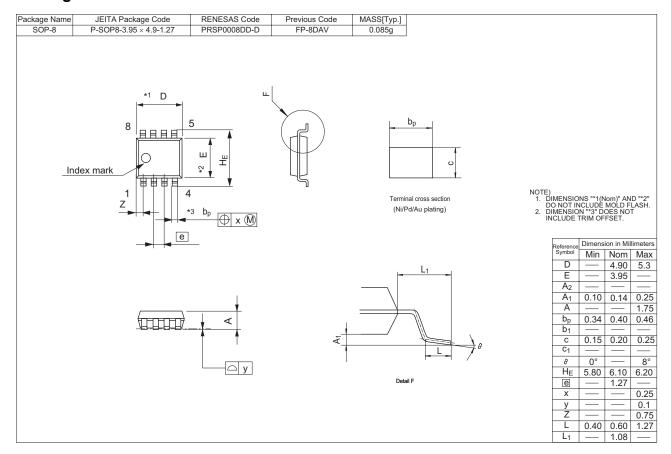








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT1038R-EL-E	2500 pcs	Taping
HAT1038RJ-EL-E	2500 pcs	Taping

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